

L Number	Hits	Search Text	DB	Time stamp
1	0	10/034279	USPAT	2004/05/11 15:37
2	0	(high adj voltage adj semiconductor) and (metal adj4 sufficient adj thickness adj3 carry adj2 high adj current)	USPAT	2004/05/11 15:39
3	0	(high adj voltage adj semiconductor) and (metal adj4 sufficient adj thickness adj4 high adj current)	USPAT	2004/05/11 15:39
4	0	(high adj voltage adj semiconductor) and (metal adj5 sufficient adj thickness adj5 high adj current)	USPAT	2004/05/11 15:40
5	0	(high adj voltage adj semiconductor adj device) and (metal adj5 sufficient adj thickness adj7 high adj current) and interconnect	USPAT	2004/05/11 15:41
6	0	(high adj voltage adj semiconductor adj device) and (metal adj5 sufficient adj thickness) and interconnect	USPAT	2004/05/11 15:43
7	1	("6008127").PN.	USPAT	2004/05/11 15:43
8	1	(("6008127").PN.) and (thickness or sufficient or high or current or carry or plurality or voltage or semiconductor or device or interconnect or ground or bottom or metal)	USPAT	2004/05/11 15:48
9	1	("6359374").PN.	USPAT	2004/05/11 15:47
10	1	(("6359374").PN.) and (thickness or sufficient or high or current or carry or plurality or voltage or semiconductor or device or interconnect or ground or bottom or metal)	USPAT	2004/05/11 15:48
-	2	10/115160	USPAT	2004/05/11 09:26
-	1	("6709903").PN.	USPAT	2004/05/11 09:26
-	1	("6562703").PN.	USPAT	2004/05/11 09:27
-	1	("6593191").PN.	USPAT	2004/05/11 09:27
-	1	((("6709903").PN.) and ("650" or degree or Si\$Ge\$ or relax or epitaxial or low or density or threading or dislocation or single or crystalline or surface or nearly or pseudomorphic or temperature or ion or implantaing or impanation or vacuum or CVD or annealing or heat or anneal or SOI or substrate)	USPAT	2004/05/11 09:31
-	1	((("6562703").PN.) and ("650" or degree or Si\$Ge\$ or relax or epitaxial or low or density or threading or dislocation or single or crystalline or surface or nearly or pseudomorphic or temperature or ion or implantaing or impanation or vacuum or CVD or annealing or heat or anneal or SOI or substrate)	USPAT	2004/05/11 09:34
-	1	((("6593191").PN.) and ("650" or degree or Si\$Ge\$ or relax or epitaxial or low or density or threading or dislocation or single or crystalline or surface or nearly or pseudomorphic or temperature or ion or implantaing or impanation or vacuum or CVD or annealing or heat or anneal or SOI or substrate)	USPAT	2004/05/11 09:35
-	17	Si\$Ge\$ and "650" and degrees and substrate and SOI and temperature and single and crystalline	USPAT	2004/05/11 10:13

5/11/04